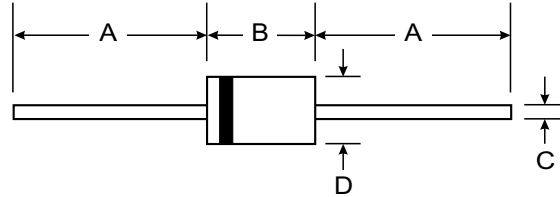


Features

- For general purpose applications
- This diode features very low turn-on voltage and fast switching. These devices are protected by a PN junction guard ring against excessive oltage, such as electrostatic discharges



DO-35		
Dim	Min	Max
A	25.40	—
B	—	4.00
C	—	0.60
D	—	2.00
All Dimensions in mm		

Mechanical Data

- Case: JEDEC DO-35, glass case
- Polarity: Color band denotes cathode end
- Weight: Approx. 0.13 gram

Maximum Ratings and Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

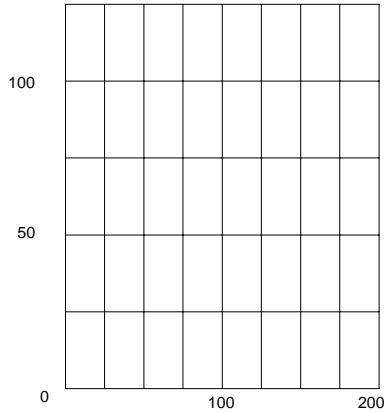
	Symbols	Value	UNITS		
Continuous reverse voltage	V_{RRM}	100	V		
Forward continuous current @ $T_A=25^\circ\text{C}$	I_F	100 ¹⁾	mA		
Repetitive peak forward current tp 1s, 0.5	I_{FRM}	350 ¹⁾	mA		
Surge forward current @tp 10ms	I_{FSM}	750 ¹⁾	mA		
Power dissipation @ $T_A=95^\circ\text{C}$	P_{tot}	100 ¹⁾	mW		
Junction temperature	T_J	-55 ---+ 125	$^\circ\text{C}$		
Ambient operating temperature range	T_L	230	$^\circ\text{C}$		
Storage temperature range	T_{STG}	-55 ---+ 150	$^\circ\text{C}$		
	Symbols	Min.	Typ.	Max.	UNITS
Reverse breakdown voltage @ $I_R=100\mu\text{A}, T_J=25^\circ\text{C}$	V_{BR}	100	-	-	V
Forward voltage @ $I_F=1\text{mA}, T_J=25^\circ\text{C}$	V_F	-	0.4	0.45	V
@ $I_F=200\text{mA}, T_J=25^\circ\text{C}$		-	-	1.0	
Leakage current @ $T_J=25^\circ\text{C}$	I_R	-	-	0.1	μA
$V_R=50\text{V}$ @ $T_J=100^\circ\text{C}$		-	-	20	
Junction capacitance at $V_R=1\text{V}, f=1\text{MHz}$	C_J	-	-	20	pF
Thermal resistance junction to ambient	$R_{\theta JA}$	-	-	300 ¹⁾	$^\circ\text{C}/\text{W}$

1) On infinite heatsink with 4mm lead length.

2) Pulse test tp<300 μs , $\Delta T < 2\%$

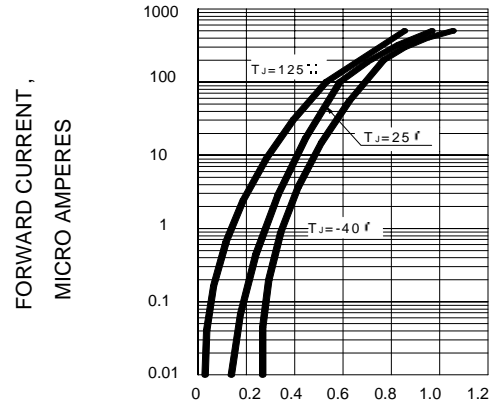


FIG.1 – ADMISSIBLE POWER DISSIPATION VS. AMBIENT TEMPERATURE



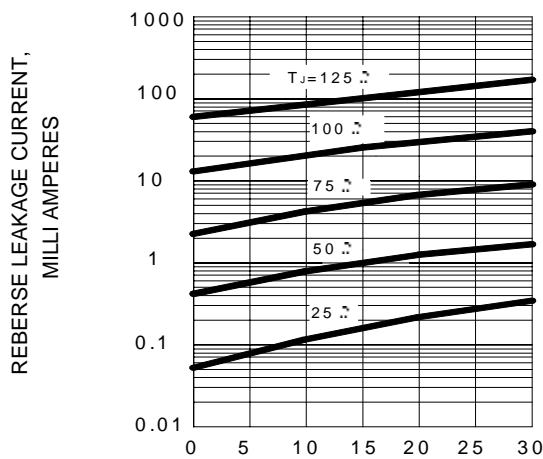
AMBIENT TEMPERATURE()

FIG.2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



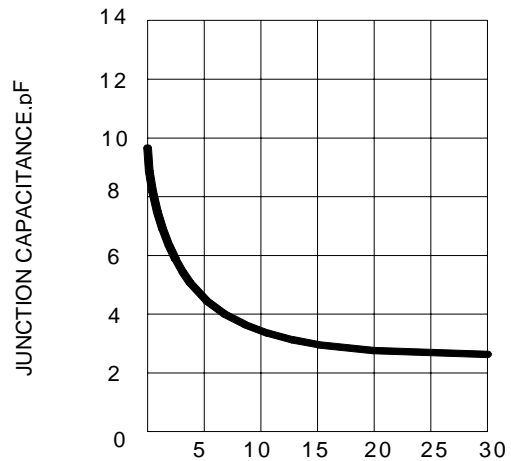
FORWARD VOLTAGE,VOLT

FIG.3 – TYPICAL REVERSE CHARACTERISTICS



REVERSE VOLTAGE, VOLT

FIG.4 – TYPICAL JUNCTION CAPACITANCE



REVERSE VOLTAGE, VOLT